

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): Milan R. Kokta, et al.

Title: MATERIALS FOR USE IN OPTICAL AND OPTOELECTRONIC APPLICATIONS

Application No.: NEW APPLICATION Filed: HEREWITH

Atty. Docket No.: 1035-BI3918-CIP

MS PATENT APPLICATION
COMMISSIONER FOR PATENTS
PO Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT TRANSMITTAL

Dear Sir:

Pursuant to 37 C.F.R. § 1.56, § 1.97 and § 1.98, the undersigned brings the patents, publications, applications or other information identified in the attached:

- ☒ Form(s) PTO/SB/08A and/or PTO/SB/08B
☐ Other: n/a

to the Examiner's attention in the above-identified application. These references were cited in parent Application No. , filed . Accordingly, in accordance with C.F.R. §1.98(d), copies of the references are not being supplied herewith. Citation of such information shall not be construed as:

1. an admission that the information necessarily is, or corresponds to, prior art with respect to the instant invention;
2. a representation that a search has been made, other than as described below; or
3. an admission that the information cited herein is, or is considered to be, material to patentability as defined in § 1.56(b).

For each item of information listed that is not in the English language, the undersigned has provided a concise explanation of the relevance, such as through (i) an English language abstract, (ii) an English language equivalent application, (iii) reference to discussion in the application, or (iv) if cited in a search report or other action by a foreign patent office in a counterpart foreign application, an English language version of the search report or action that indicates the degree of relevance found by the foreign office.

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STATEMENT UNDER 37 C.F.R. § 1.704(d)

If the above-identified application is an original application filed on or after
May 29, 2000:

- ☐ each item of information contained in this Information Disclosure Statement was cited in a communication from a foreign patent office in a counterpart application and this communication was not received by any individual designated in § 1.56(c) more than thirty days prior to the filing of this Information Disclosure Statement.

FEES DUE

This Information Disclosure Statement is being filed:

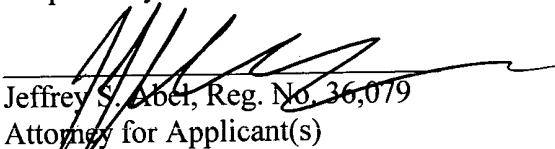
- ☒ within three months of the filing date of a national application or within three months of entry of the national stage as set forth in § 1.491 in an international application. Therefore, no fee is required.
- ☐ before the mailing date of a first Office action on the merits or before the mailing date of a first Office action after the filing of a request for continued examination under § 1.114. Therefore, no fee is believed required.
- ☐ after the period specified in § 1.97(c), but on or before payment of the issue fee. Accordingly, the fee set forth in § 1.17(p) is required and provided as shown on the attached Fee Transmittal.

If however, this Information Disclosure Statement is determined by the USPTO to be filed after the period specified in § 1.97(b), the undersigned hereby authorizes the Commissioner to charge the fee set forth in § 1.17(p) as shown on the attached Fee Transmittal.

Date

7/23

Respectfully submitted,


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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

Substitute for form 1449/PTO

Complete if Known
Application Number **NEW APPLICATION**
Filing Date **HEREWITH**
First Named Inventor **Milan R. Kokta**
Attorney Docket Number **1035-BI3918-CIP**

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| Examiner Initials * | Cite No. 1 | U.S. Patent Document Number | Kind Code 2 (if known) | Name of Patentee or Applicant of Cited Document | Date of Publication of Cited Document MM-DD-YYYY | Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear |
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| | BM | | | | | | | <input type="checkbox"/> |

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